CSD88537ND Dual 60-V N-Channel NexFET™ Power MOSFET

1 Features

- Ultra-Low Q_g and Q_{gd}
- Avalanche Rated
- Pb Free
- RoHS Compliant
- Halogen Free

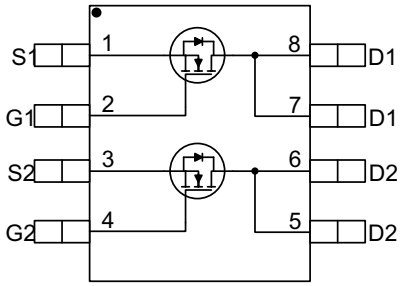
2 Applications

- Half Bridge for Motor Control
- Synchronous Buck Converter

3 Description

This dual SO-8, 60 V, 12.5 mΩ NexFET™ power MOSFET is designed to serve as a half bridge in low current motor control applications.

Top View



Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	60		V
Q_g	Gate Charge Total (10 V)	14		nC
Q_{gd}	Gate Charge Gate-to-Drain	2.3		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 6 V	15	mΩ
		V_{GS} = 10 V	12.5	mΩ
$V_{GS(th)}$	Threshold Voltage	3.0		V

Ordering Information(1)

Device	Media	Qty	Package	Ship
CSD88537ND	13-Inch Reel	2500	SO-8 Plastic Package	Tape and Reel
CSD88537NDT	7-Inch Reel	250		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

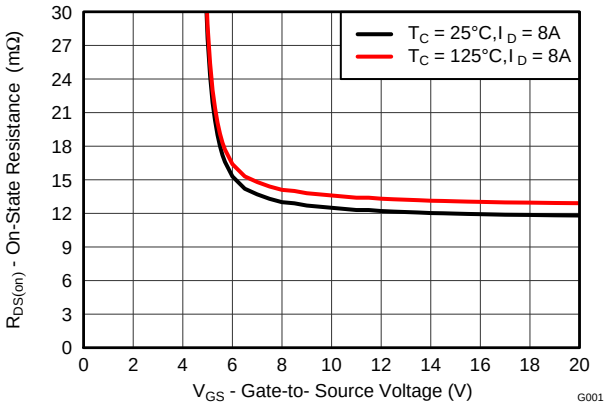
Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited)	15	A
	Continuous Drain Current (Silicon limited), T_C = 25°C	16	
	Continuous Drain Current (1)	8.0	
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	108	A
P_D	Power Dissipation(1)	2.1	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 32, L = 0.1 mH, R_G = 25 Ω	51	mJ

(1) Typical $R_{\theta JA}$ = 60°C/W on a 1-inch², 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.

(2) Max $R_{\theta JL}$ = 20°C/W, pulse duration ≤100 µs, duty cycle ≤1%

$R_{DS(on)}$ vs V_{GS}



Gate Charge

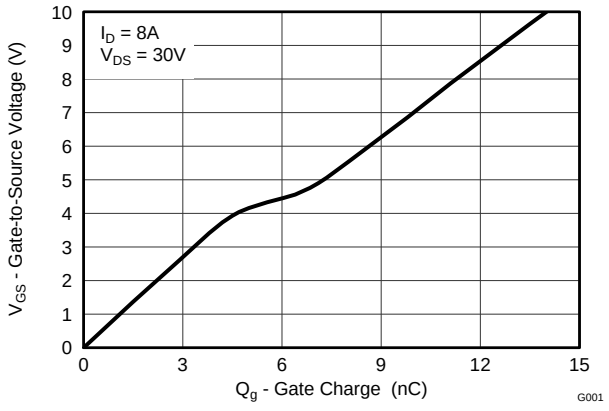


Table of Contents

4 Revision History

Changes from Original (January 2014) to Revision A **Page**

- Pulsed drain current increased from 62 to 108 A ... 1
- Updated pulsed drain current conditions ... 1
- Changed $R_{\theta JC}$ to $R_{\theta JL}$ in *Thermal Information* ... 3
- Updated the SOA in Figure 10 ... 6

5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 250 µA	60			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0 V, V_{DS} = 48 V			1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	2.6	3	3.6	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 6 V, I_D = 8 A		15	19	mΩ
		V_{GS} = 10 V, I_D = 8 A		12.5	15	mΩ
g_{fs}	Transconductance	V_{DS} = 30 V, I_D = 8 A		42		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 30 V, f = 1 MHz		1080	1400	pF
C_{oss}	Output Capacitance			133	173	pF
C_{rss}	Reverse Transfer Capacitance			4	5.2	pF
R_G	Series Gate Resistance			5.5	11	Ω
Q_g	Gate Charge Total (10 V)	V_{DS} = 30 V, I_D = 8 A		14	18	nC
Q_{gd}	Gate Charge Gate-to-Drain			2.3		nC
Q_{gs}	Gate Charge Gate-to-Source			4.6		nC
$Q_{g(th)}$	Gate Charge at V_{th}			3.4		nC
Q_{oss}	Output Charge	V_{DS} = 30 V, V_{GS} = 0 V		25		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 30 V, V_{GS} = 10 V, I_{DS} = 8 A, R_G = 0 Ω		6		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn Off Delay Time			5		ns
t_f	Fall Time			19		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 8 A, V_{GS} = 0 V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 30 V, I_F = 8 A, di/dt = 300 A/µs		50		nC
t_{rr}	Reverse Recovery Time			30		ns

5.2 Thermal Information

(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JL}$	Junction-to-Lead Thermal Resistance(1)			20	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance(1)(2)			75	

(1) $R_{\theta JL}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inches × 1.5-inches (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JL}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.

5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

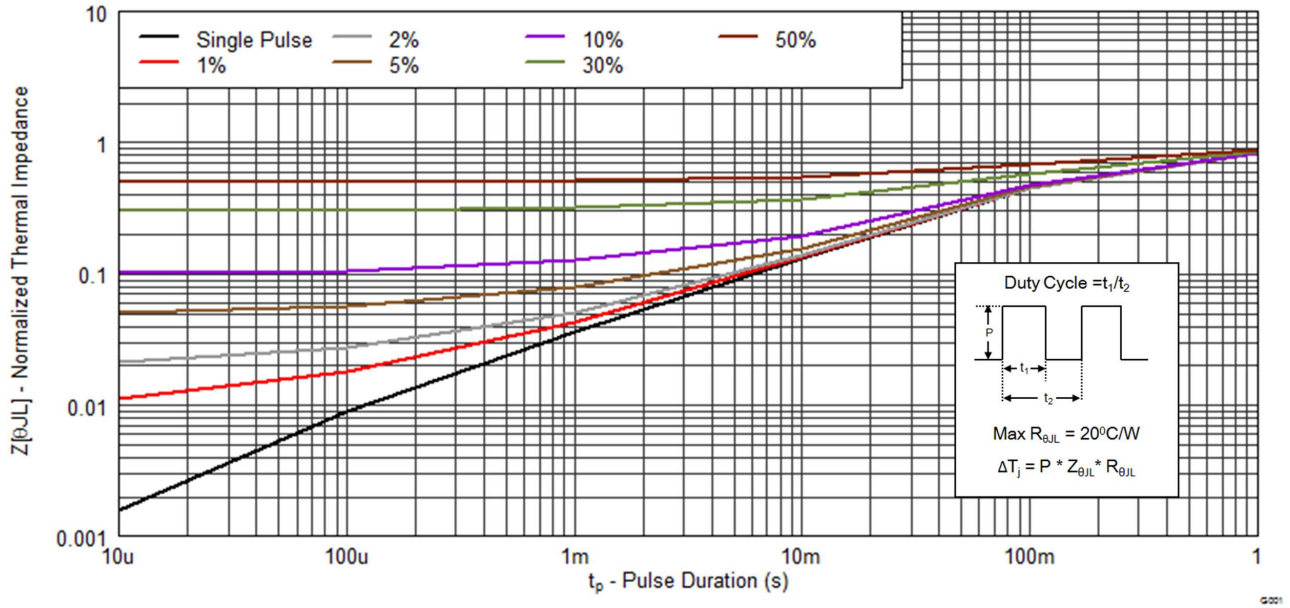


Figure 1. Transient Thermal Impedance

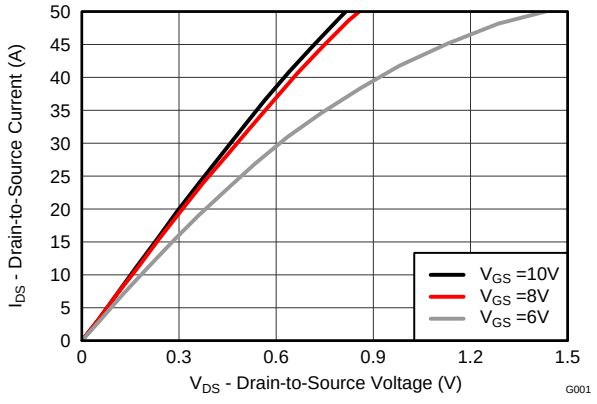


Figure 2. Saturation Characteristics

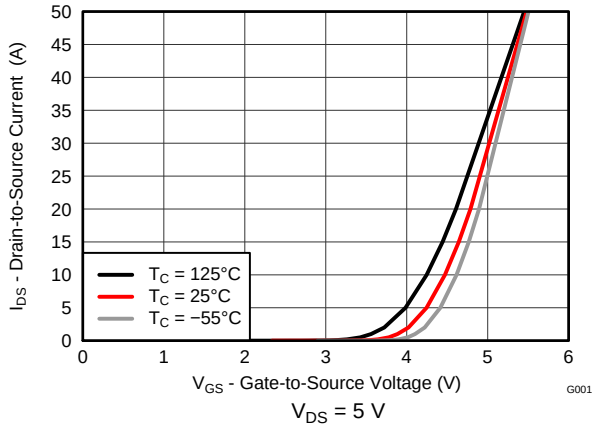


Figure 3. Transfer Characteristics

Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

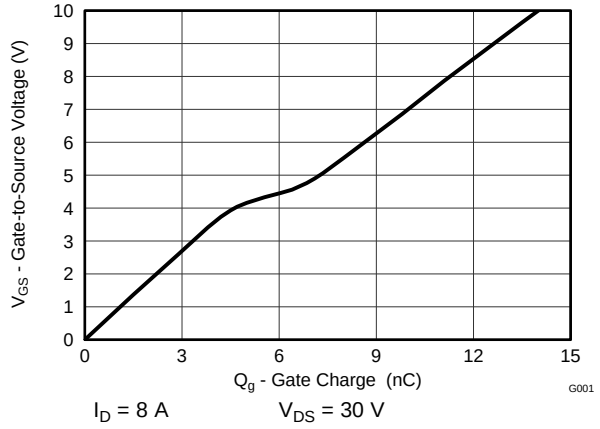


Figure 4. Gate Charge

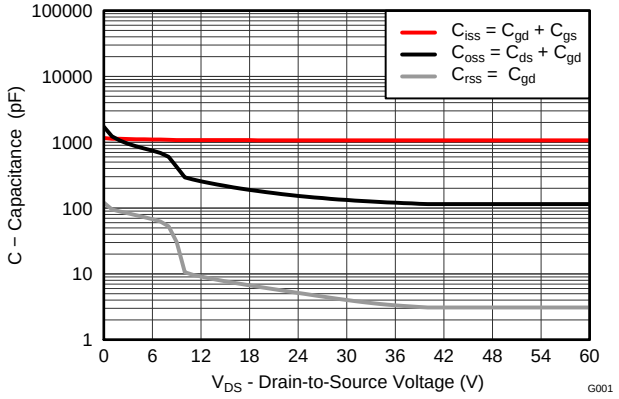


Figure 5. Capacitance

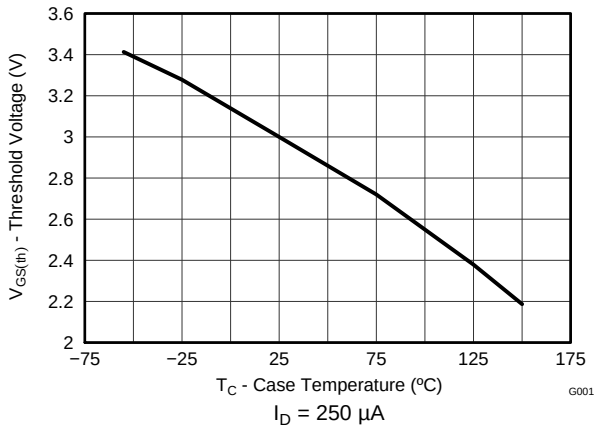


Figure 6. Threshold Voltage vs Temperature

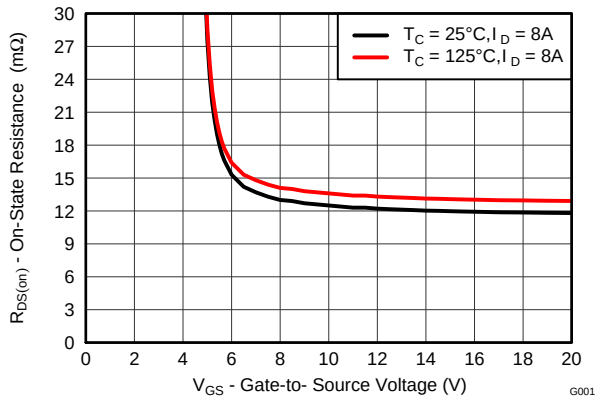


Figure 7. On-State Resistance vs Gate-to-Source Voltage

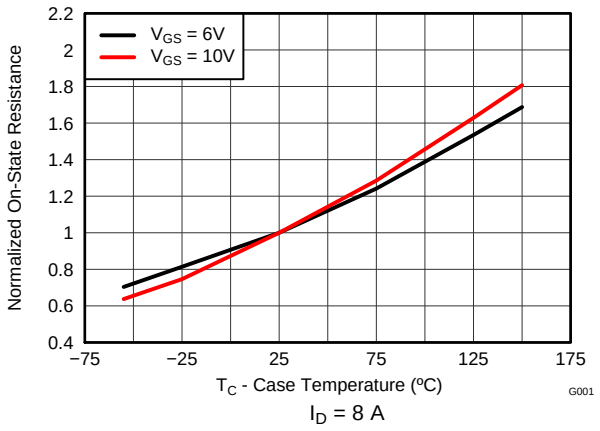


Figure 8. Normalized On-State Resistance vs Temperature

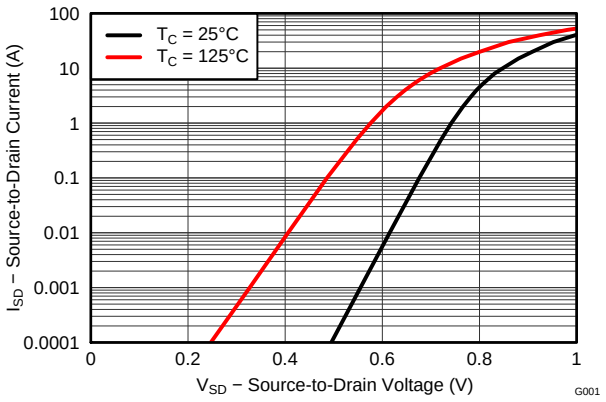


Figure 9. Typical Diode Forward Voltage

Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

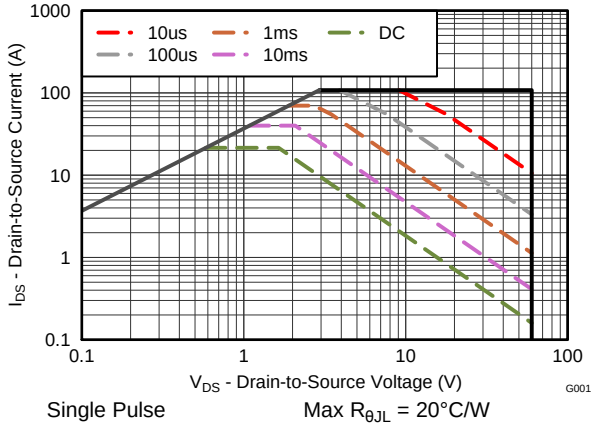


Figure 10. Maximum Safe Operating Area

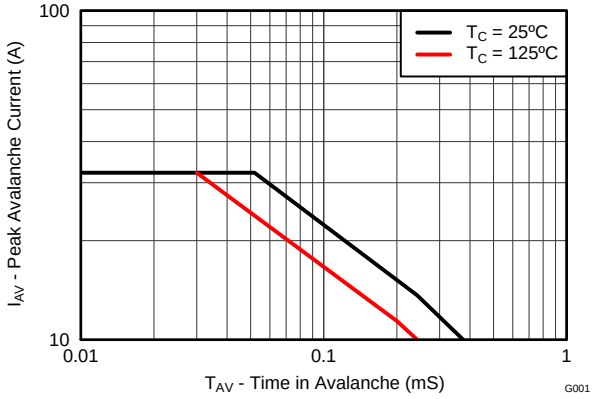


Figure 11. Single Pulse Unclamped Inductive Switching

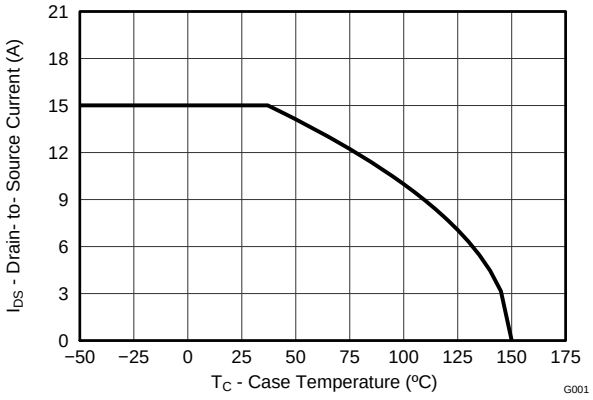


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

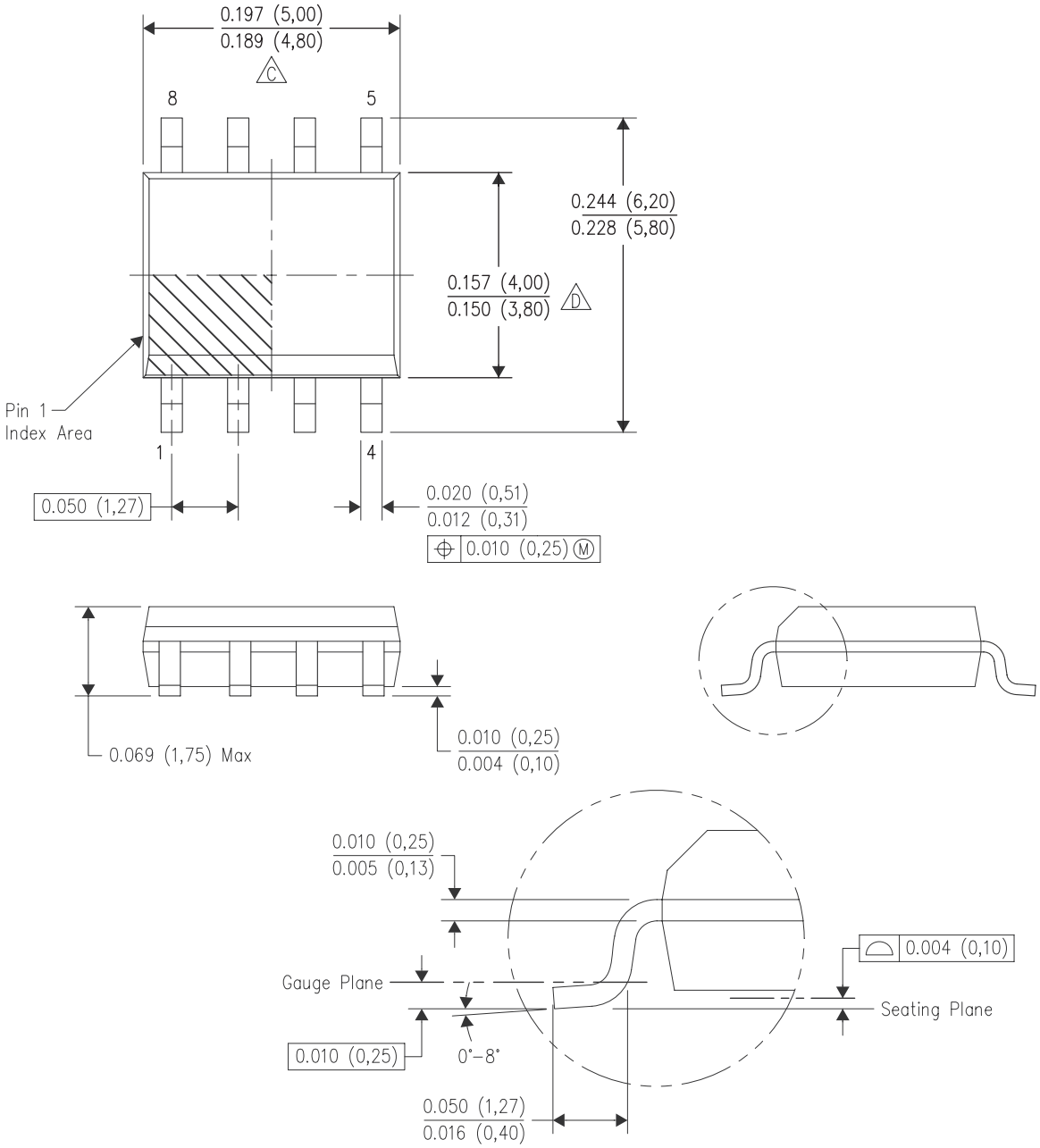
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

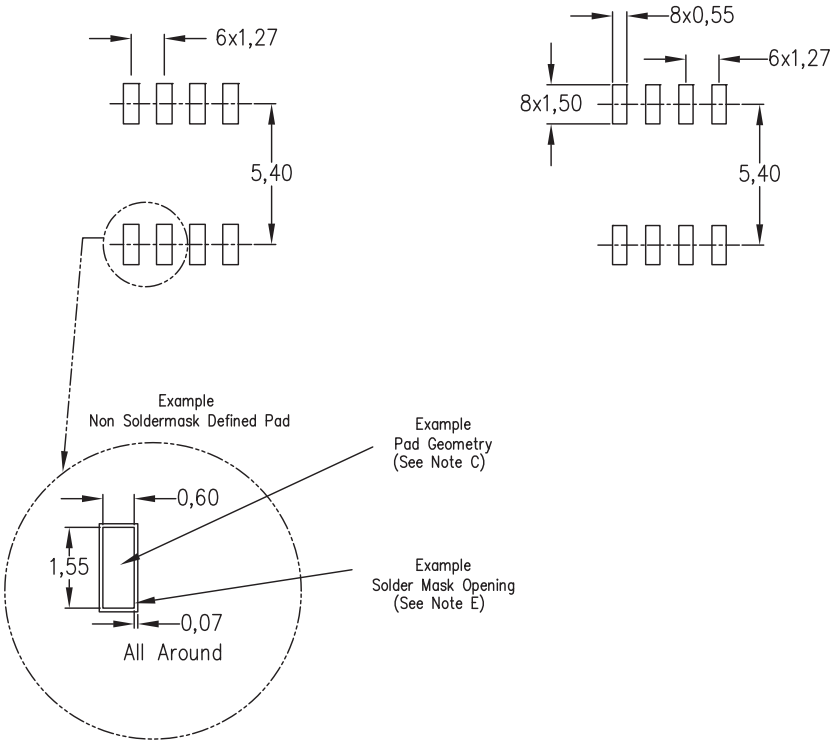
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 SO-8 Package Dimensions



1. All linear dimensions are in inches (millimeters).
2. This drawing is subject to change without notice.
3. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0.15) each side.
4. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0.43) each side.
5. Reference JEDEC MS-012 variation AA.

7.2 Recommended PCB Pattern and Stencil Opening



1. All linear dimensions are in millimeters.
2. This drawing is subject to change without notice.
3. Publication IPC-7351 is recommended for alternate designs.
4. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
5. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD88537ND	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 150	88537N	Samples
CSD88537NDT	ACTIVE	SOIC	D	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 150	88537N	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265